

Silicon NPN Power Transistors

2SC940

DESCRIPTION

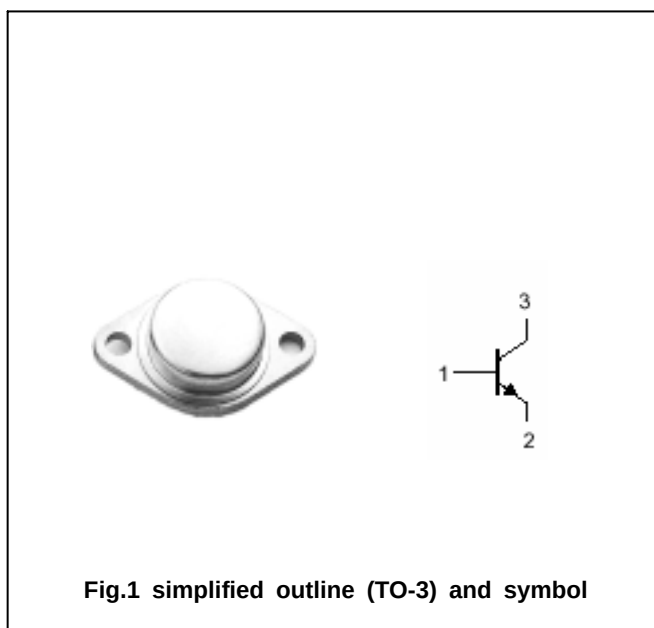
- With TO-3 package
- High current capability
- Wide area of safe operation

APPLICATIONS

- For B/W TV horizontal deflection application

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	90	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		7.5	A
I_{CM}	Collector current-peak		15	A
P_T	Total power dissipation	$T_{mb}=25^\circ\text{C}$	50	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA ; I _B =0	90			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A ; I _B =0.5A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =90V ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V ; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =5A ; V _{CE} =5V	15		70	
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V		20		MHz

◆ h_{FE-2} Classifications

O	Q	P
15-35	25-45	35-70

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PACKAGE OUTLINE

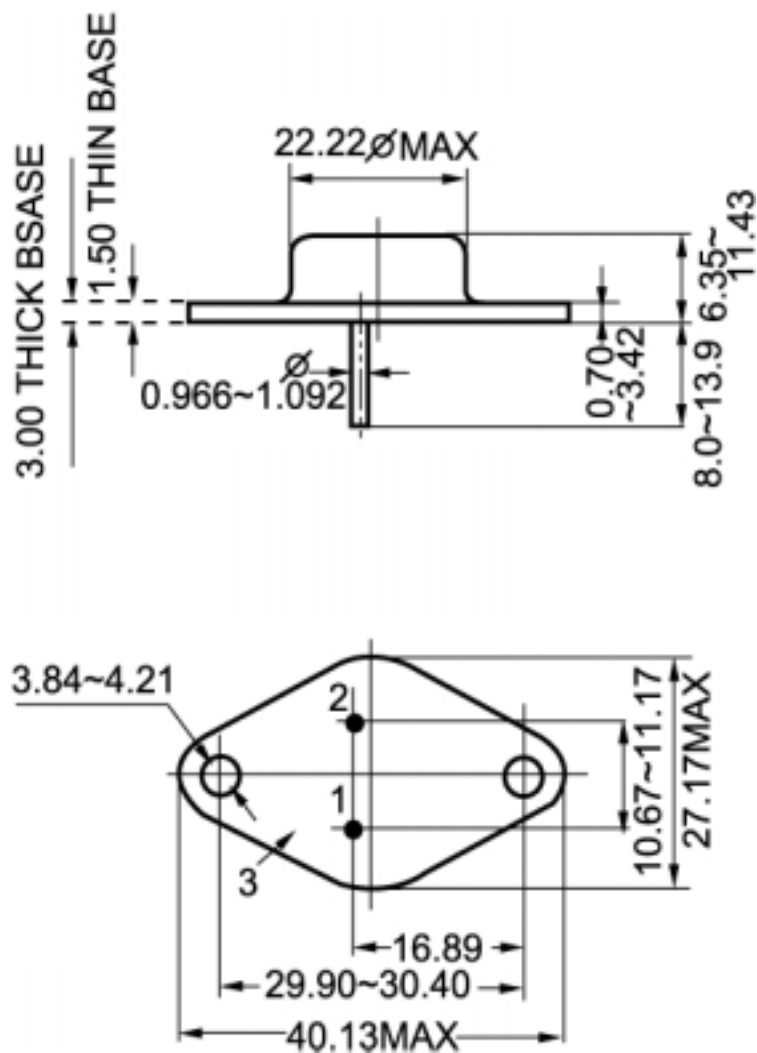


Fig.2 Outline dimensions